MOSFETs Silicon P-Channel MOS (U-MOSVI)

# SSM3J76CT

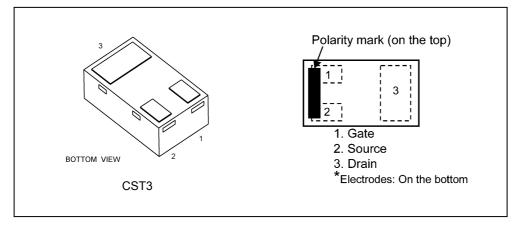
## 1. Applications

High-Speed Switching

## 2. Features

- (1) 1.2 V drive
- (2) Low drain-source on-resistance
  - $\begin{array}{l} : \mathrm{R}_{\mathrm{DS(ON)}} = 390 \ \mathrm{m}\Omega \ (\mathrm{max}) \ (@\mathrm{V}_{\mathrm{GS}} = -4.5 \ \mathrm{V}) \\ \mathrm{R}_{\mathrm{DS(ON)}} = 480 \ \mathrm{m}\Omega \ (\mathrm{max}) \ (@\mathrm{V}_{\mathrm{GS}} = -2.5 \ \mathrm{V}) \\ \mathrm{R}_{\mathrm{DS(ON)}} = 660 \ \mathrm{m}\Omega \ (\mathrm{max}) \ (@\mathrm{V}_{\mathrm{GS}} = -1.8 \ \mathrm{V}) \\ \mathrm{R}_{\mathrm{DS(ON)}} = 900 \ \mathrm{m}\Omega \ (\mathrm{max}) \ (@\mathrm{V}_{\mathrm{GS}} = -1.5 \ \mathrm{V}) \\ \mathrm{R}_{\mathrm{DS(ON)}} = 4000 \ \mathrm{m}\Omega \ (\mathrm{max}) \ (@\mathrm{V}_{\mathrm{GS}} = -1.2 \ \mathrm{V}) \end{array}$
- (3) Low leakage current

## 3. Packaging and Pin Assignment



## 4. Absolute Maximum Ratings (Note) (Unless otherwise specified, $T_a = 25$ °C)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V <sub>DSS</sub>	-20	V
Gate-source voltage		V <sub>GSS</sub>	±8	
Drain current (DC)	(Note 1)	I <sub>D</sub>	-1.4	A
Drain current (pulsed)	(Note 1), (Note 2)	I <sub>DP</sub>	-2.8	
Power dissipation	(Note 3)	PD	500	mW
Channel temperature		T <sub>ch</sub>	150	°C
Storage temperature		T <sub>stg</sub>	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Ensure that the channel temperature does not exceed 150 °C.

Note 2: Pulse width (PW)  $\leq$  10 ms, duty = 1 %

Note 3: Device mounted on a 25.4 mm × 25.4 mm × 1.6 mm FR4 glass epoxy board (Cu pad: 645 mm<sup>2</sup>)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

- Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.
- Note: The channel-to-ambient thermal resistance, R<sub>th(ch-a)</sub>, and the drain power dissipation, P<sub>D</sub>, vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.

## 5. Electrical Characteristics

## 5.1. Static Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	$V_{GS}$ = ±5 V, $V_{DS}$ = 0 V	_	—	±0.08	μA
			V <sub>GS</sub> = ±8 V, V <sub>DS</sub> = 0 V	_		±1	
Drain cut-off current		I <sub>DSS</sub>	V <sub>DS</sub> = -20 V, V <sub>GS</sub> = 0 V	_		-0.08	
Drain-source breakdown voltage		V <sub>(BR)DSS</sub>	I <sub>D</sub> = -1 mA, V <sub>GS</sub> = 0 V	-20		_	V
Drain-source breakdown voltage	(Note 1)	V <sub>(BR)DSX</sub>	I <sub>D</sub> = -1 mA, V <sub>GS</sub> = 5 V	-15	_	—	
Gate threshold voltage	(Note 2)	V <sub>th</sub>	V <sub>DS</sub> = -3 V, I <sub>D</sub> = -1 mA	-0.3	_	-1.0	
Drain-source on-resistance	(Note 3)	R <sub>DS(ON)</sub>	$I_{\rm D}$ = -800 mA, $V_{\rm GS}$ = -4.5 V	_	310	390	mΩ
			I <sub>D</sub> = -500 mA, V <sub>GS</sub> = -2.5 V	—	380	480	
			I <sub>D</sub> = -200 mA, V <sub>GS</sub> = -1.8 V	—	470	660	
			I <sub>D</sub> = -100 mA, V <sub>GS</sub> = -1.5 V	_	560	900	
			I <sub>D</sub> = -10 mA, V <sub>GS</sub> = -1.2 V	—	770	4000	
Forward transfer admittance	(Note 3)	Y <sub>fs</sub>	V <sub>DS</sub> = -3 V, I <sub>D</sub> = -100 mA	0.5	1.0	_	S

Note 1: If a forward bias is applied between gate and source, this device enters V<sub>(BR)DSX</sub> mode. Note that the drainsource breakdown voltage is lowered in this mode.

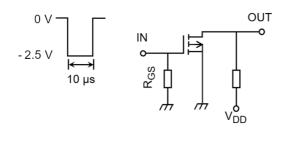
Note 2: Let  $V_{th}$  be the voltage applied between gate and source that causes the drain current (I<sub>D</sub>) to below (-1 mA for this device). Then, for normal switching operation,  $V_{GS(ON)}$  must be higher than  $V_{th}$ , and  $V_{GS(OFF)}$  must be lower than  $V_{th}$ . This relationship can be expressed as:  $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$ . Take this into consideration when using the device.

Note 3: Pulse measurement.

## 5.2. Dynamic Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -10 V, V <sub>GS</sub> = 0 V,	_	100	_	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1 MHz	_	10	—	
Output capacitance	C <sub>oss</sub>		_	16	—	
Switching time (turn-on time)	t <sub>on</sub>	V <sub>DD</sub> = -10 V, I <sub>D</sub> = -200 mA V <sub>GS</sub> = 0 to -2.5 V, R <sub>GS</sub> = 50 Ω		8	—	ns
Switching time (turn-off time)	t <sub>off</sub>	Duty $\leq$ 1 %, V <sub>IN</sub> : t <sub>r</sub> , t <sub>f</sub> < 5 ns, Common source, See Chapter 5.3.		26	_	

## 5.3. Switching Time Test Circuit



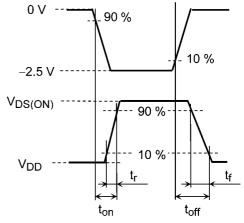


Fig. 5.3.1 Switching Time Test Circuit

Fig. 5.3.2 Input Waveform/Output Waveform

## 5.4. Gate Charge Characteristics (Unless otherwise specified, $T_a = 25$ °C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD}$ = -10 V, $V_{GS}$ = -4.5 V,	_	1.6		nC
Gate-source charge 1	Q <sub>gs1</sub>	I <sub>D</sub> = -800 mA	_	0.2	—	
Gate-drain charge	Q <sub>gd</sub>		_	0.4	_	

## 5.5. Source-Drain Characteristics (Unless otherwise specified, $T_a = 25$ °C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	(Note 1)	$V_{DSF}$	I <sub>D</sub> = 1.4 A, V <sub>GS</sub> = 0 V	_	1.0	1.3	V

Note 1: Pulse measurement.

### 6. Marking

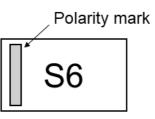


Fig. 6.1 Marking

## 7. Equivalent Circuit

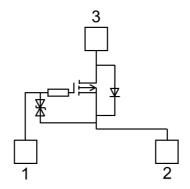
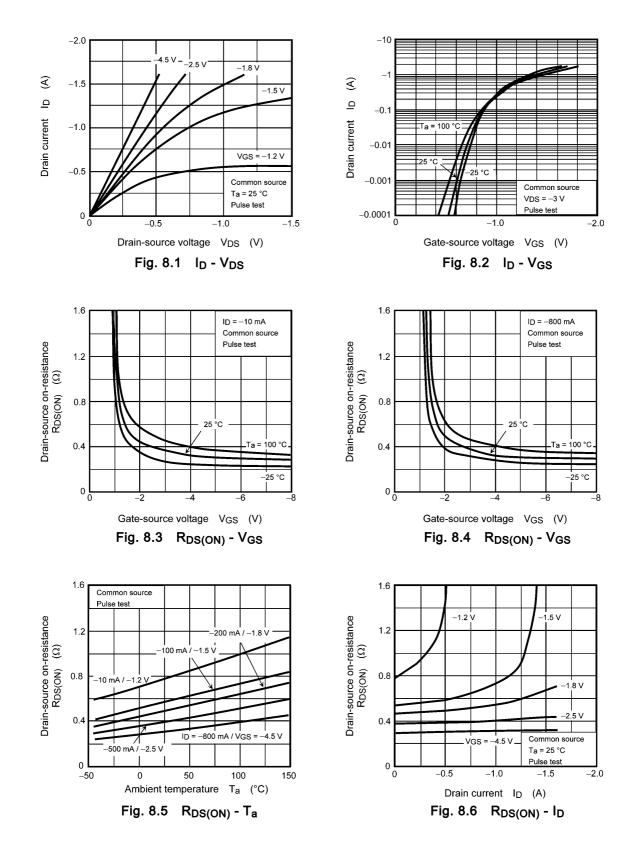


Fig. 7.1 Equivalent Circuit

## 8. Characteristics Curves (Note)



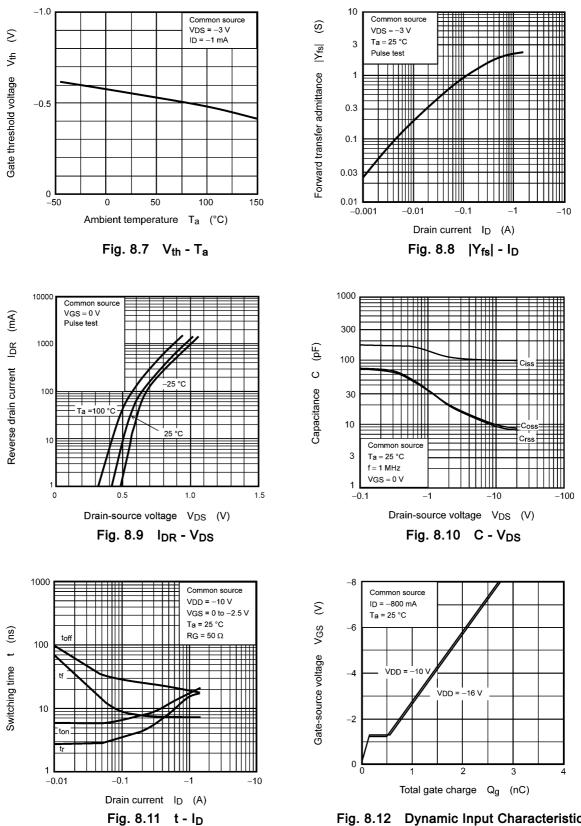
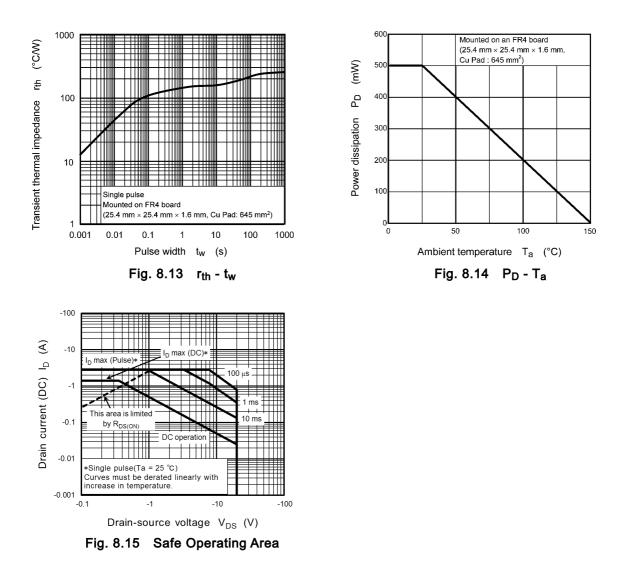


Fig. 8.12 Dynamic Input Characteristics



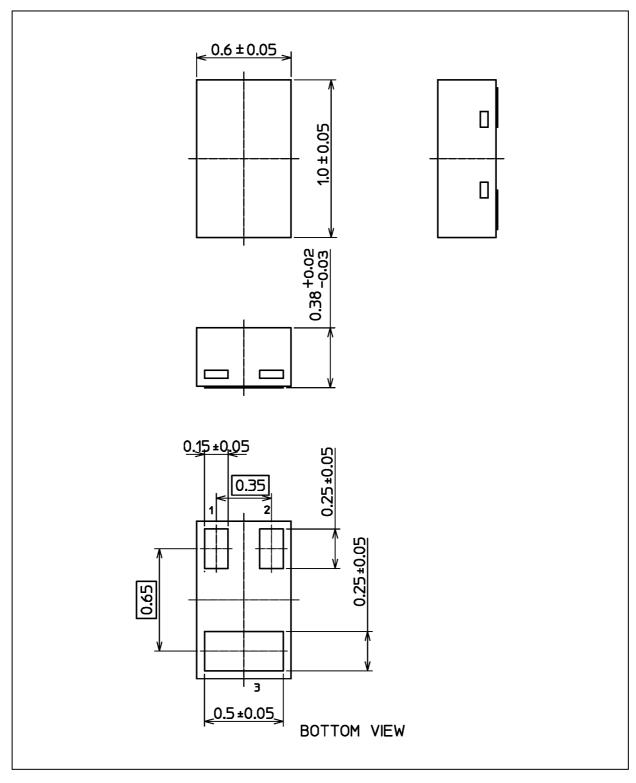
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



## SSM3J76CT

## **Package Dimensions**

Unit: mm



#### Weight: 0.75 mg (typ.)

	Package Name(s)
JEDEC: SOT-883	
Nickname: CST3	

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